

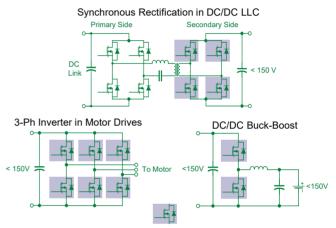




High Current (≥ 100 A) 300 V X3-Class Ultra Junction HiPerFET™

The high current 300 V Ultra Junction X3-Class HiPerFETTM devices from Littelfuse feature some of the lowest on-state resistances, as low as $5.5 \text{ m}\Omega$ in the TO-264 package and $4.6 \text{ m}\Omega$ in the SOT-227B (miniBLOCTM).

Developed using a charge compensation principle and proprietory process, these 300 V HiPerFETs have one of the best-inclass figure of merit, $R_{\text{DS(on)}}$ X Q_{g} (on-state resistance x gate-charge). Additionally, the fast body diode in these HiPerFETs featuring low reverse recovery charge and recovery time results in high efficiency in applications. These devices also display superior dv/dt performance and robust avalanche capability. These competitive benefits enable designers to address several design challenges in various applications.



300 V X3-Class HiPerFET™

$R_{DS(on),max}$	I _{D25}	TO-268-HV	TO-247	PLUS247	TO-264	SOT-227B
13.5	100	IXFT100N30X3HV	IXFH100N30X3	_	_	_
11	120	IXFT120N30X3HV	IXFH120N30X3	_	_	_
8.3	150	IXFT150N30X3HV	IXFH150N30X3	_	IXFK150N30X3	_
5.5	210	-	-	IXFX210N30X3	IXFK210N30X3	_
4.6	210	_	-	_	_	IXFN210N30X3

Features

- Low R_{DS(on)} and high current capability
- Low gate charge Q_a
- Fast body diode with reduced Q_{rr} and t_{rr}
- Reduced junction-case thermal resistance R_{th.IC}
- High power dissipation capability
- Superior dv/dt and high avalanche energy rating



Benefits

- Compact design with high power density
- Reduced paralleling effort and decreased part count
- Simplified driver reduces design effort
- Cost-efficient solution with ease of assembly
- Competitive thermal performance
- Improved reliability in application

Applications

- Industrial and process power supplies
- Telecom and data center power supplies
- Battery formation
- Battery energy storage systems
- DC load switch
- Robotics and servo controls



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